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DISCLOSURE STATEMENT	:	Applicant: Berger
BY APPLICANTS	:	Group Art Unit: 2811
		Examiner: Nadav

OTHER DOCUMENTS

1. Amlani, I. et al., Digital Logic Gate Using Quantum-Dot Cellular Automata, *Science*, 284, pp. 289-291 (April 9, 1999).
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Examiner	Date Considered
CRANE	8/2005

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U.S. PATENT DOCUMENTS

Examiner's Initial	Document Number	Date	Name	Class/Sub-class
	NONE			

FOREIGN PATENT DOCUMENTS

Examiner's Initial	Document Number	Date	Country/Name	Translation yes/no
	NONE			

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